Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- · Logic-level compatible
- · Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- · Relay driver
- · High-speed line driver
- · High-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	$V_{GS} = -10 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	-6	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -4.6 A; T_j = 25 °C		-	35	45	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D
2	D	drain		
3	G	gate		G \downarrow \downarrow \downarrow
4	S	source	TSOP6 (SOT457)	
5	D	drain		
6	D	drain		S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMN50EPE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN50EPE	3L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-6	Α
		V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-4.6	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-2.9	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-19	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	560	mW
			[1]	-	1.4	W
		T _{sp} = 25 °C		-	6.25	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode				<u>'</u>	
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.4	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

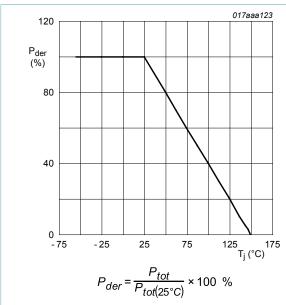


Fig. 1. Normalized total power dissipation as a function of junction temperature

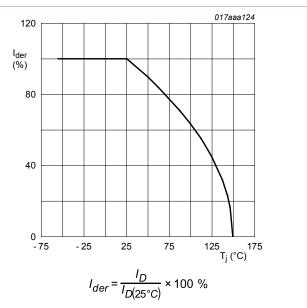


Fig. 2. Normalized continuous drain current as a function of junction temperature

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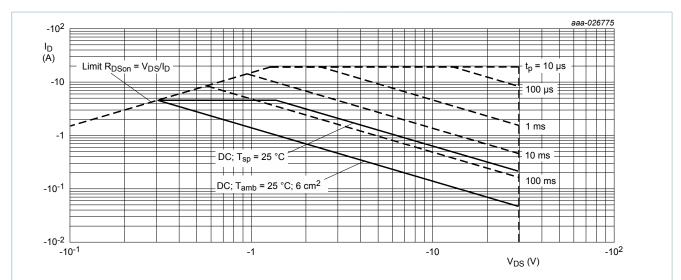


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	195	225	K/W
			<u>[2]</u>	-	78	90	K/W
		in free air; t ≤ 5 s	[2]	-	55	63	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	15	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

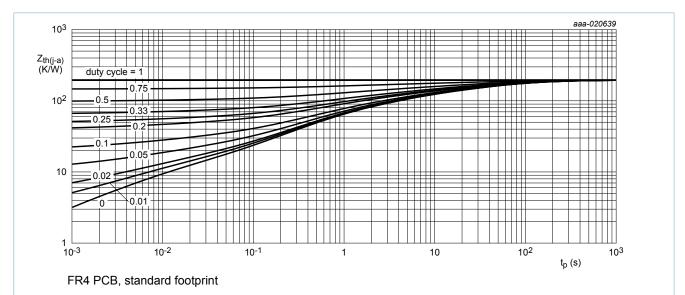


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

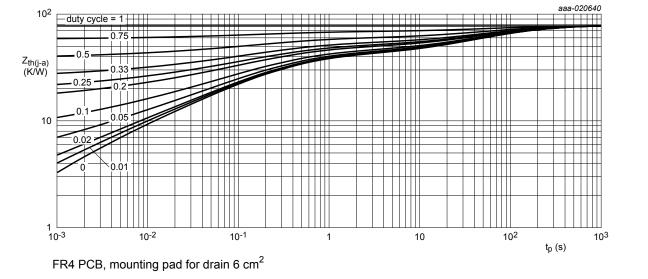


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics			'		
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-1	-2	-3	V
I _{DSS}	drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μA
R _{DSon}	drain-source on-state	$V_{GS} = -10 \text{ V}; I_D = -4.6 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	35	45	mΩ
	resistance	V _{GS} = -10 V; I _D = -4.6 A; T _j = 150 °C	-	51	67	mΩ
		$V_{GS} = -4.5 \text{ V}; I_D = -3.6 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	49	72	mΩ
9fs	forward transconductance	V_{DS} = -10 V; I_D = -4.6 A; T_j = 25 °C	-	14.2	-	S
R _G	gate resistance	f = 1 MHz	-	13	-	Ω
Dynamic cl	haracteristics		,			
Q _{G(tot)}	total gate charge	V_{DS} = -15 V; I_{D} = -4.2 A; V_{GS} = -10 V;	-	12.8	20	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	2.2	-	nC
Q _{GD}	gate-drain charge		-	2.2	-	nC
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	793	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	134	-	pF
C _{rss}	reverse transfer capacitance		-	84	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -15 \text{ V}; I_D = -4.2 \text{ A}; V_{GS} = -10 \text{ V};$	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	19	-	ns
$t_{d(off)}$	turn-off delay time		-	36	-	ns
t _f	fall time		-	19	-	ns
Source-dra	in diode					
V_{SD}	source-drain voltage	I _S = -1.4 A; V _{GS} = 0 V; T _i = 25 °C	_	-0.8	-1.2	V

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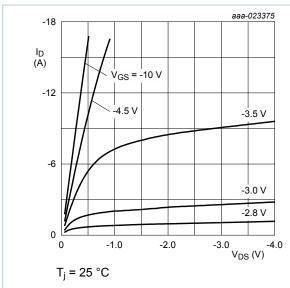


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

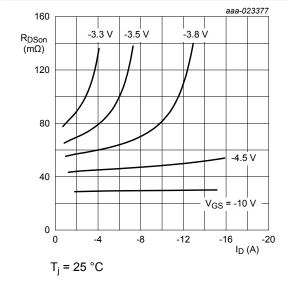


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

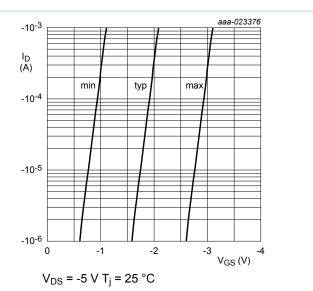


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

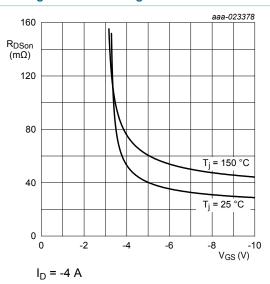


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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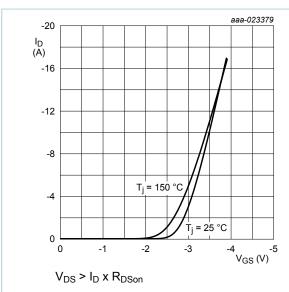


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

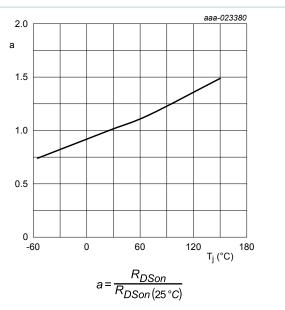


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

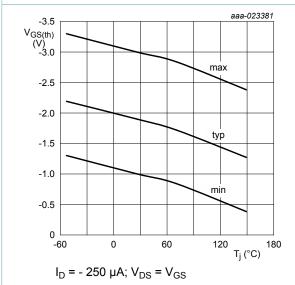


Fig. 12. Gate-source threshold voltage as a function of junction temperature

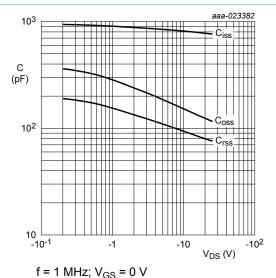


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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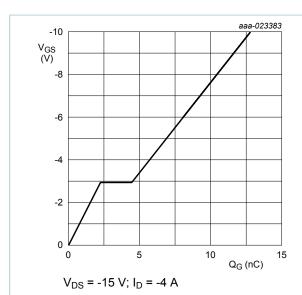


Fig. 14. Gate-source voltage as a function of gate charge; typical values

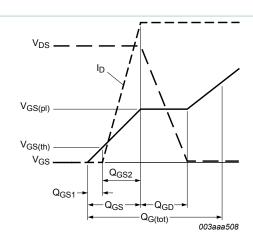


Fig. 15. Gate charge waveform definitions

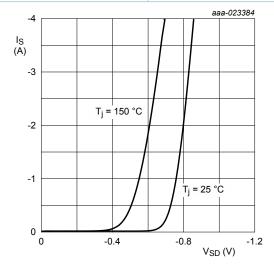
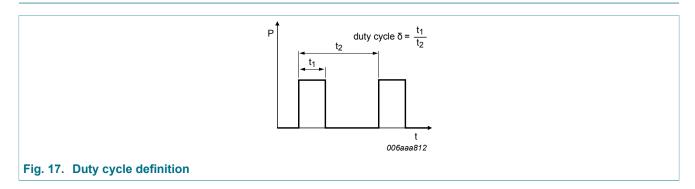


Fig. 16. Source current as a function of source-drain voltage; typical values

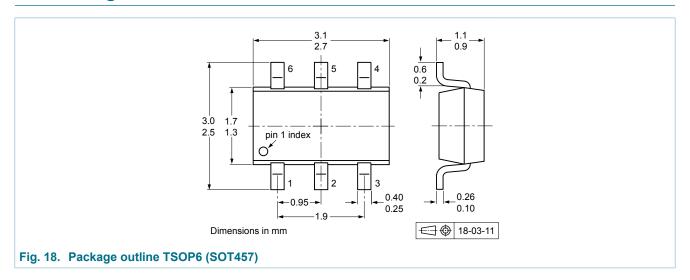
 $V_{GS} = 0 V$

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11. Test information

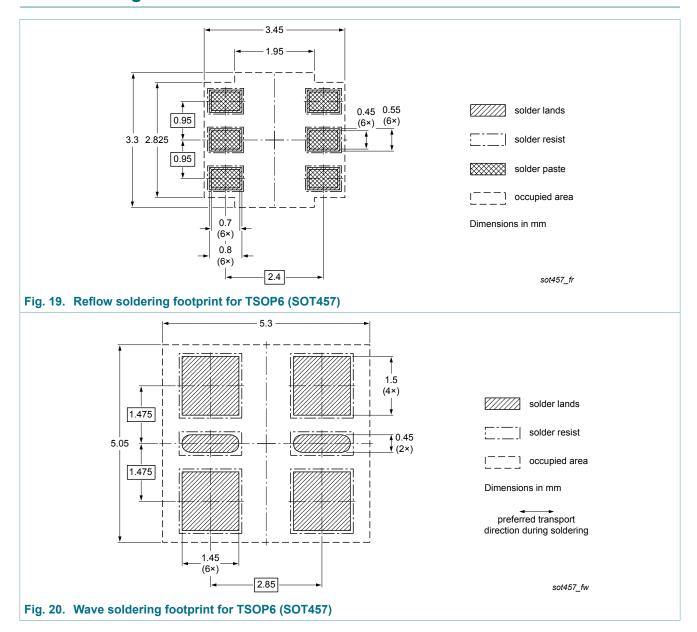


12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN50EPE v.1	20180416	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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